L Number	Hits	Search Text	DB	Time stamp
_	570		USPAT	2003/06/03 14:36
_	294		USPAT	2004/08/30 16:13
_	215		USPAT	2002/07/02 13:55
	213	conductor)	OSTAT	2002/07/02 13:33
_	111		USPAT	2002/01/24 17:17
	111	conductor)	ODIAI	2002/01/21 1/.1/
_	72	i e e e e e e e e e e e e e e e e e e e	USPAT;	2002/07/12 16:15
_	12		US-PGPUB;	2002/07/12 10:15
		(resistor adj film)		
			EPO; JPO;	
			DERWENT;	İ
	200	057/526	IBM_TDB	0000/07/03 00:00
_	320		USPAT;	2002/07/03 09:20
		conductor)	US-PGPUB;	
			EPO; JPO;	
İ			DERWENT;	İ
			IBM_TDB	0000/07/00 00 01
_	12	, , , , , , , , , , , , , , ,	USPAT;	2002/07/03 09:34
		conductor)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		0.57/505	IBM_TDB	0000/07/07 55 55
-	12	, , ,	USPAT;	2002/07/05 08:50
1		conductor)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	12		USPAT;	2002/07/03 11:28
	·	conductor)	US-PGPUB;	
	İ		EPO; JPO;	
}			DERWENT;	
			IBM_TDB	
-	63	,	USPAT;	2002/07/03 14:53
		conductor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	72	438/381 and resistor and conductor	USPAT;	2002/07/08 07:54
İ			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	226	, , ,	USPAT;	2003/06/03 16:36
		conduct\$3) and substrate and (wiring or	US-PGPUB;	
		terminal)	EPO; JPO;	
			DERWENT;	1
	1300	257/526	IBM_TDB	2002/10/20 15:50
-	1382	257/536	USPAT;	2003/10/30 15:50
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		057/506 1 1 1 1	IBM TDB	2002/10/20 15 25
-	1321	257/536 and resist\$5	USPAT;	2003/10/30 16:06
			US-PGPUB;	
]		EPO; JPO;	
		,	DERWENT;	
		257/526	IBM_TDB	2004/05/10 11 01
-	42	257/536 and resist\$5 and wiring and	USPAT;	2004/05/12 11:01
		substrate and (silicon adj oxide)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		057/506	IBM_TDB	0000/10/20 15 15
_	22		USPAT;	2003/10/30 16:29
		conduct\$4)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	l i
	<u> </u>		IBM_TDB	

				10004/05/10 10 50
-	21	257/536 and resist\$4 and (heat adj	USPAT;	2004/05/12 10:58
		conduct\$4)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	1
			IBM_TDB	
-	19		USPAT;	2004/05/12 11:11
		substrate and (silicon adj oxide)	US-PGPUB;	1
•	į		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	46	257/536 and resist\$5 and wiring and	USPAT;	2004/05/12 11:11
i		substrate and (silicon adj oxide)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	39	257/538 and resist\$5 and wiring and	USPAT;	2004/05/12 11:32
1		substrate and (silicon adj oxide)	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	779	257/536	USPAT	2004/08/30 16:21
-	367	257/537	USPAT	2004/08/30 16:24
-	398	257/538	USPAT	2004/08/30 16:28
_	290	257/539	USPAT	2004/08/30 16:31
-	38	257/540	USPAT	2004/08/30 16:32
-	73	257/541	USPAT	2004/08/30 16:33
-	67	257/542	USPAT	2004/08/30 16:34
-	80	257/543	USPAT	2004/08/30 16:36
-	468	257/358	USPAT	2004/08/30 16:40
-	290	257/359	USPAT	2004/08/30 16:43
_	233	1 - , -	USPAT	2004/08/30 16:46
-	391	257/363	USPAT	2004/08/30 16:50
-	911	257/379	USPAT	2004/08/30 16:58
_	408	257/380	USPAT	2004/08/30 17:02
_	414	438/382	USPAT	2004/08/30 17:07
-	580	438/309	USPAT	2004/08/30 17:07